

# NTB150N65S3HF

## MOSFET – N-Channel, SUPERFET III, FRFET

650 V, 24 A, 150 mΩ

### Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power systems for miniaturization and higher efficiency. SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 121 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 43 \text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(\text{eff.})} = 400 \text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

### Applications

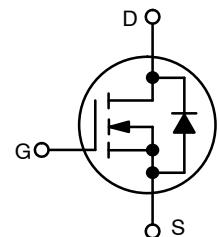
- Telecom / Server Power Supplies
- Industrial Power Supplies
- EV Charger
- UPS / Solar



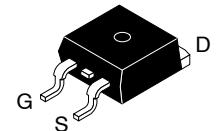
ON Semiconductor®

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$V_{DSS}$	$R_{DS(\text{ON}) \text{ MAX}}$	$I_D \text{ MAX}$
650 V	150 mΩ @ 10 V	24 A



N-CHANNEL MOSFET



D<sup>2</sup>PAK  
(TO-263 3-Lead)  
CASE 418AJ

### MARKING DIAGRAM

\$Y&Z&3&K  
NTB150  
N65S3HF

\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Data Code (Year & Week)  
&K = Lot  
NTB150N65S3HF = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# NTB150N65S3HF

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage		650	V
V <sub>GSS</sub>	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I <sub>D</sub>	Drain Current	– Continuous (T <sub>C</sub> = 25°C)	24	A
		– Continuous (T <sub>C</sub> = 100°C)	15.2	
I <sub>DM</sub>	Drain Current	– Pulsed (Note 1)	60	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		275	mJ
I <sub>AS</sub>	Avalanche Current (Note 2)		3.8	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		1.92	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	192	W
		– Derate Above 25°C	1.54	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		–55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I<sub>AS</sub> = 3.8 A, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 12 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 400 V, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	0.65	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max., (Note 4)	40	

4. Device on 1 in<sup>2</sup> 2-oz copper pad on 1.5 x 1.5 in. board of FR-4 material.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping <sup>†</sup>
NTB150N65S3HF	NTB150N65S3HF	D <sup>2</sup> PAK	330 mm	24 mm	800 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTB150N65S3HF

ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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## OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^\circ\text{C}$	650			V
		$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 150^\circ\text{C}$	700			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 15 \text{ mA}$ , Referenced to $25^\circ\text{C}$		0.62		$^\circ\text{C}$
Id <sub>SS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 650 \text{ V}, V_{GS} = 0 \text{ V}$		10		$\mu\text{A}$
		$V_{DS} = 520 \text{ V}, T_C = 125^\circ\text{C}$		67		
Ig <sub>SS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			$\pm 100$	nA

## ON CHARACTERISTICS

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 0.54 \text{ mA}$	3.0		5.0	V
$R_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$		121	150	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_D = 12 \text{ A}$		14		S

## DYNAMIC CHARACTERISTICS

$C_{iss}$	Input Capacitance	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1985		pF
$C_{oss}$	Output Capacitance			40		pF
$C_{oss(\text{eff.})}$	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$		400		pF
$C_{oss(\text{er.})}$	Energy Related Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$		71		pF
$Q_{g(\text{tot})}$	Total Gate Charge at 10 V			43		nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DS} = 400 \text{ V}, I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 5)		13		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			17		nC
ESR	Equivalent Series Resistance	$f = 1 \text{ MHz}$		5.0		$\Omega$

## SWITCHING CHARACTERISTICS

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 400 \text{ V}, I_D = 12 \text{ A}, V_{GS} = 10 \text{ V}$ $R_g = 4.7 \Omega$ (Note 5)		21		ns
$t_r$	Turn-On Rise Time			19		ns
$t_{d(\text{off})}$	Turn-Off Delay Time			63		ns
$t_f$	Turn-Off Fall Time			14		ns

## SOURCE-DRAIN DIODE CHARACTERISTICS

$I_S$	Maximum Continuous Source to Drain Diode Forward Current			24		A
$I_{SM}$	Maximum Pulsed Source to Drain Diode Forward Current			60		A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 12 \text{ A}$			1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{DD} = 400 \text{ V}, I_{SD} = 12 \text{ A},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$		88		ns
$Q_{rr}$	Reverse Recovery Charge			306		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

## TYPICAL CHARACTERISTICS

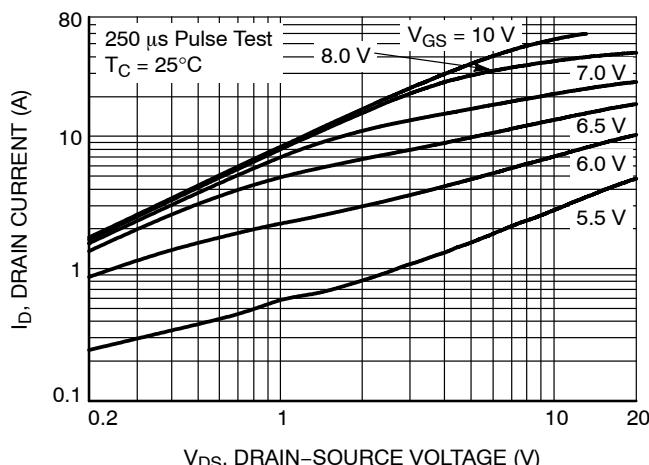


Figure 1. On-Region Characteristics

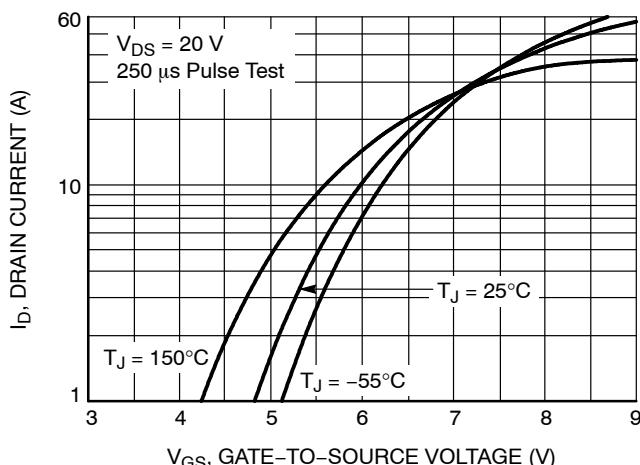


Figure 2. Transfer Characteristics

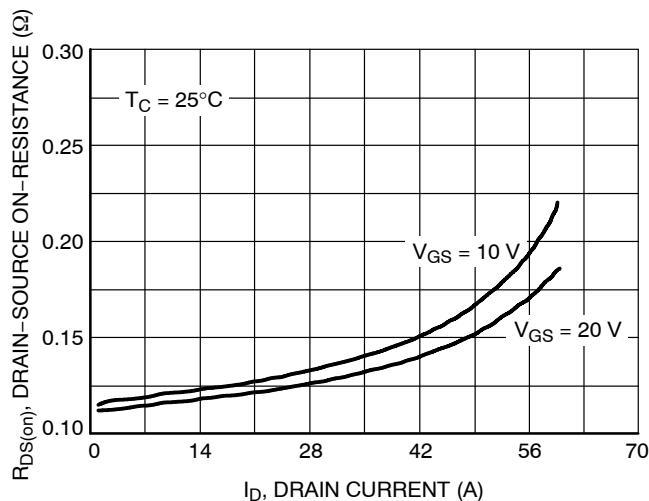


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

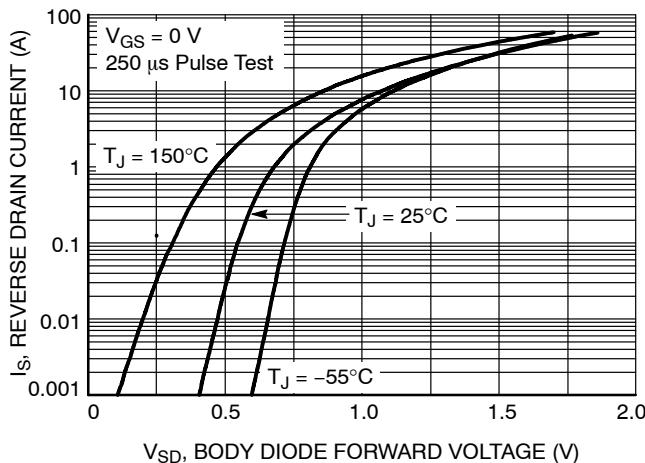


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

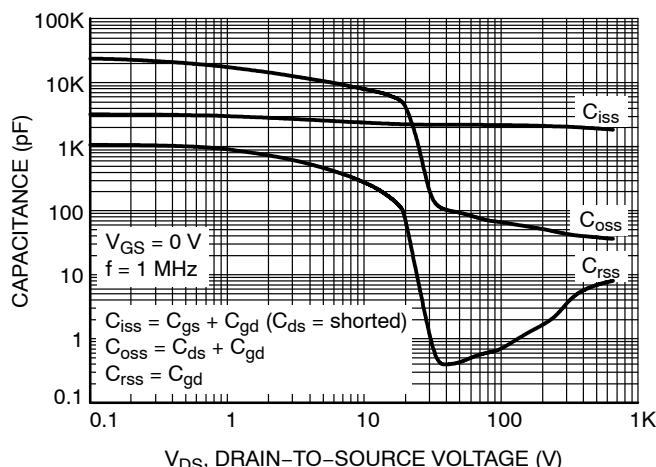


Figure 5. Capacitance Characteristics

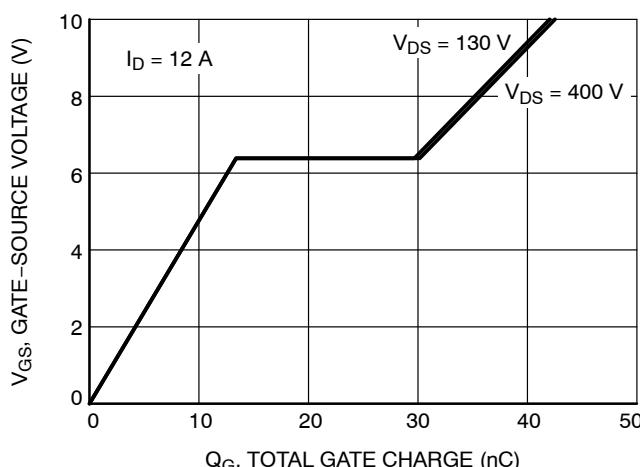
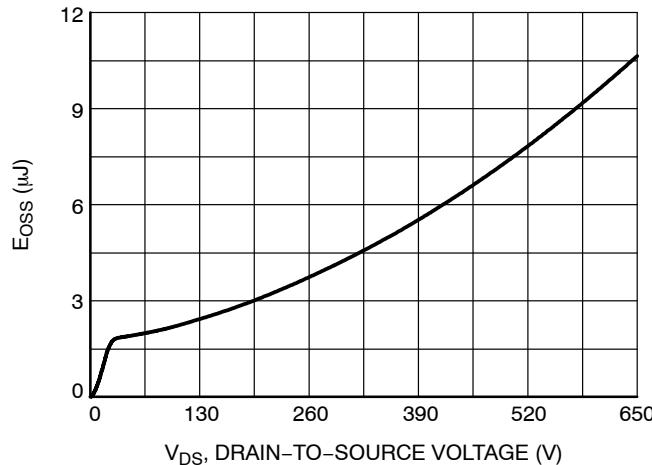
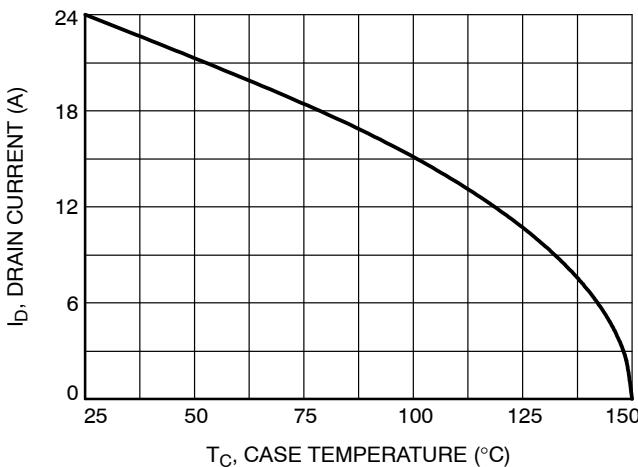
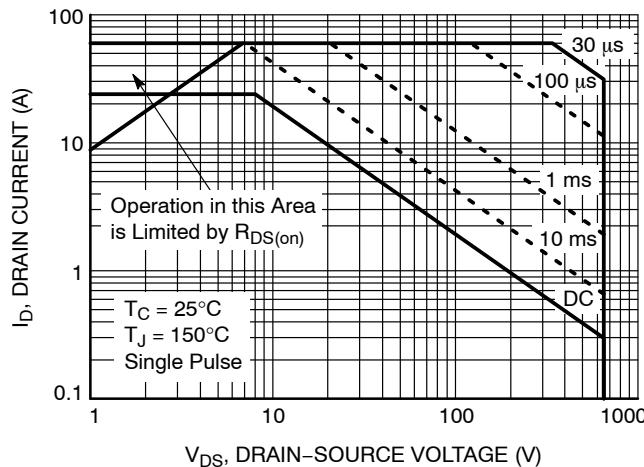
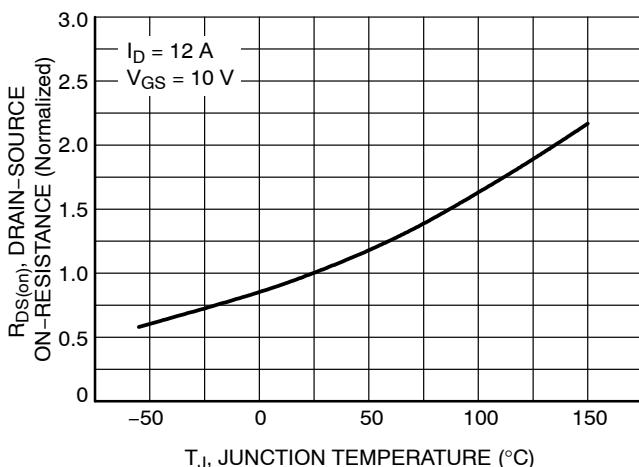
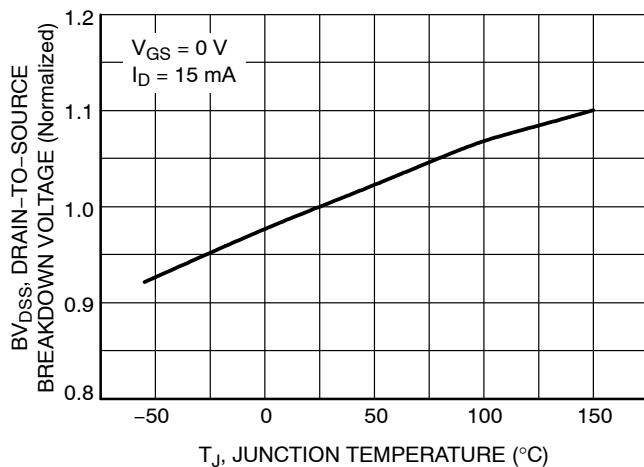


Figure 6. Gate Charge Characteristics

## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS

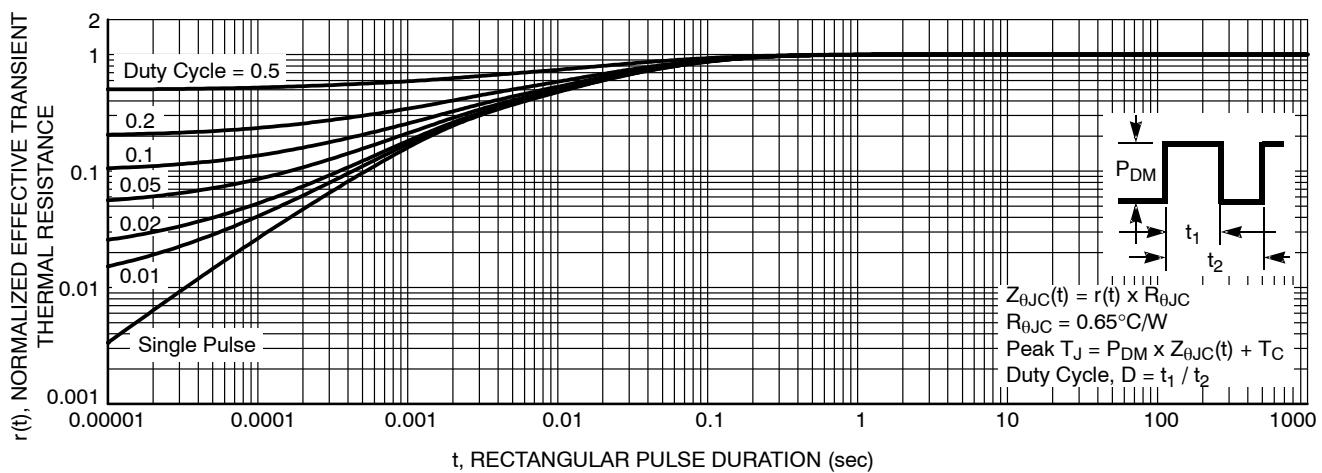


Figure 12. Transient Thermal Response Curve

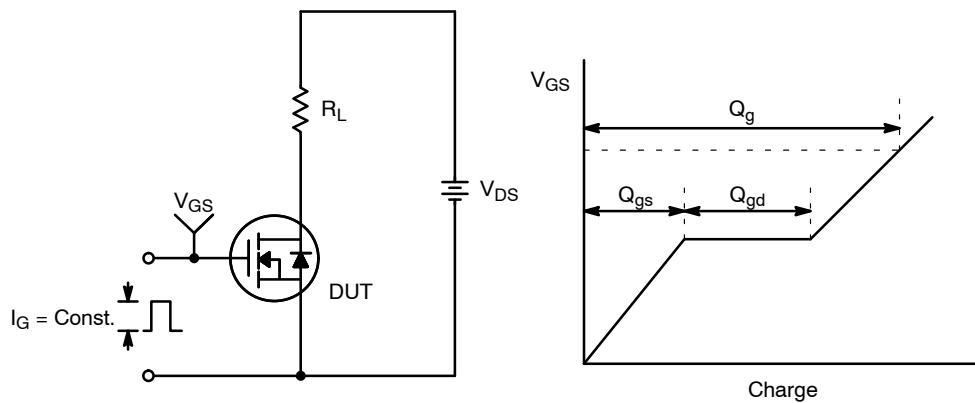


Figure 13. Gate Charge Test Circuit & Waveform

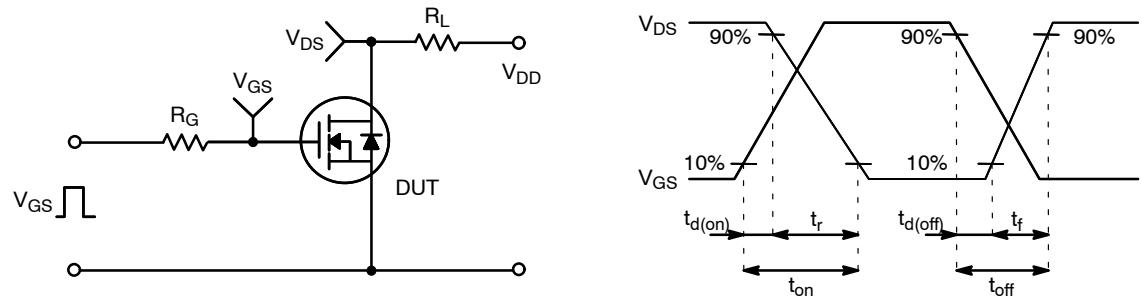


Figure 14. Resistive Switching Test Circuit & Waveforms

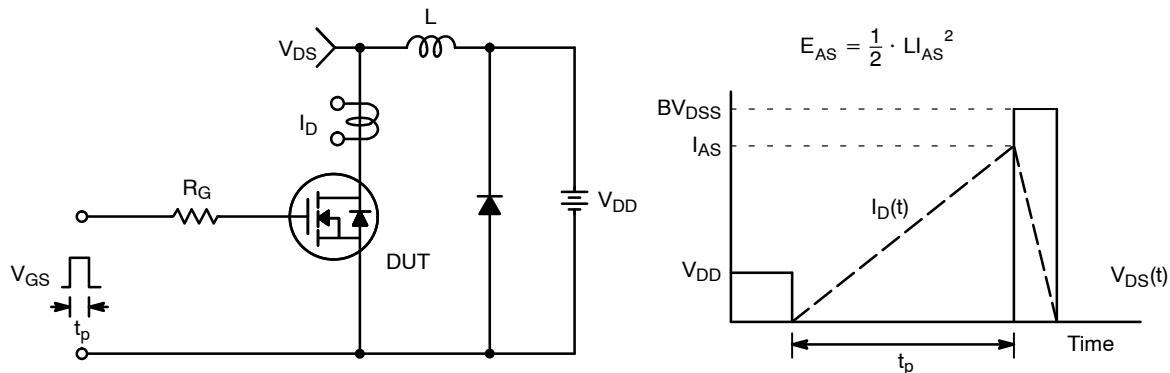


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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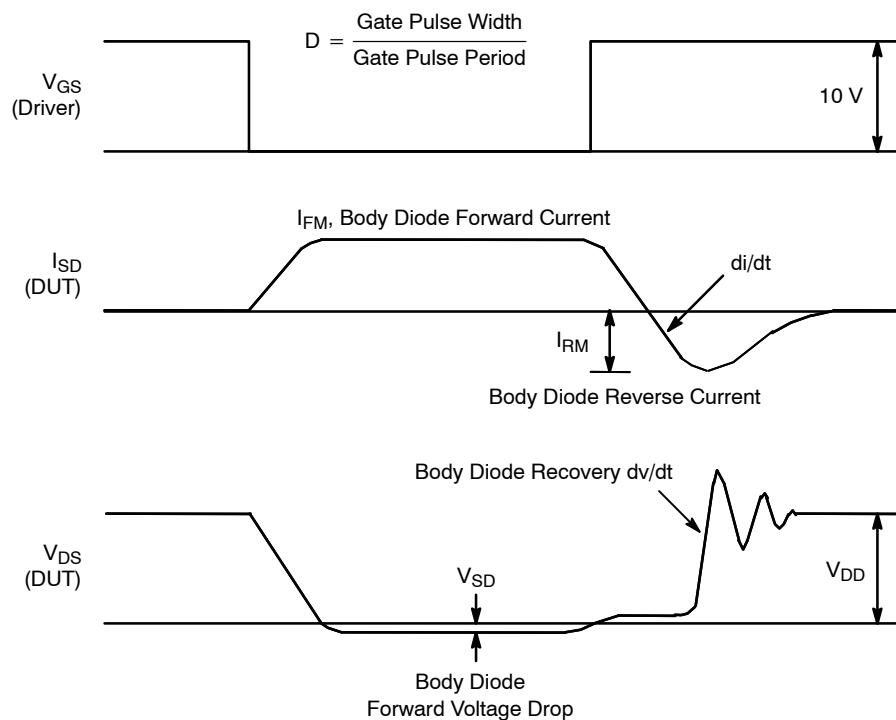
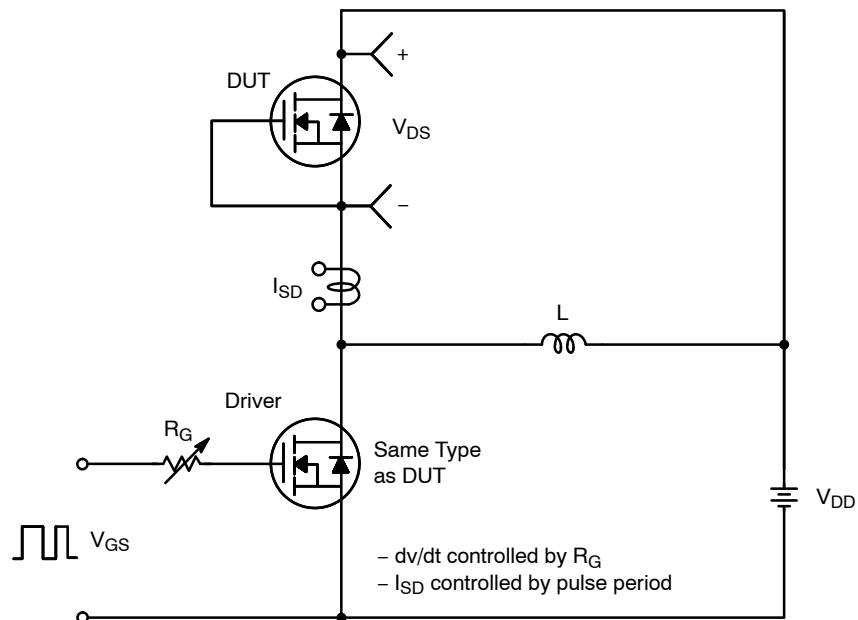


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



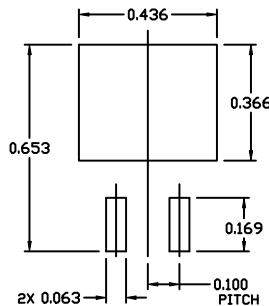
SCALE 1:1

D<sup>2</sup>PAK-3 (TO-263, 3-LEAD)

CASE 418AJ

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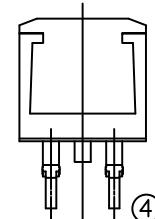
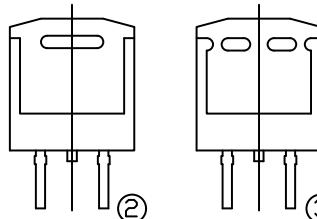
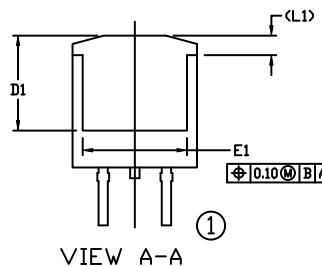
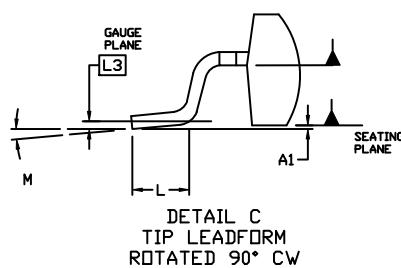
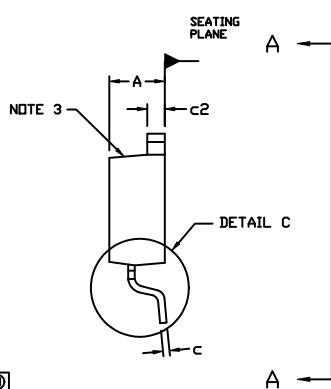
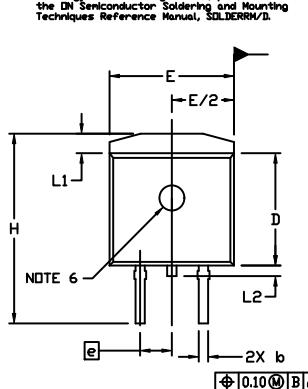
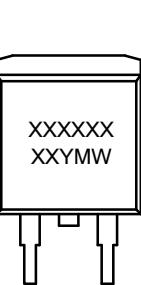
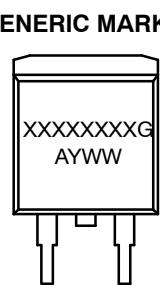
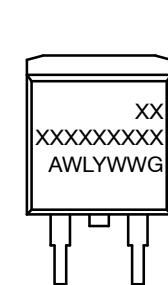
## RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRAV2.

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. CHAMFER OPTIONAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
6. OPTIONAL MOLD FEATURE.
7. ①, ② ... OPTIONAL CONSTRUCTION FEATURE CALL OUTS.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
c	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260	---	6.60	---
E	0.380	0.420	9.65	10.67
E1	0.245	---	6.22	---
e	0.100	BSC	2.54	BSC
H	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1	---	0.066	---	1.68
L2	---	0.070	---	1.78
L3	0.010	BSC	0.25	BSC
M	0°	8°	0°	8°

VIEW A-A  
OPTIONAL CONSTRUCTIONS

## GENERIC MARKING DIAGRAMS\*

XXXXXX = Specific Device Code

A = Assembly Location

WL = Wafer Lot

Y = Year

WW = Work Week

W = Week Code (SSG)

M = Month Code (SSG)

G = Pb-Free Package

AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	D <sup>2</sup> PAK-3 (TO-263, 3-LEAD)	PAGE 1 OF 1

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